

IN THE CLAIMS:

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1. (Previously Amended) A semiconductor device comprising:

- a conductive member;
- a cobalt including layer having oxidation resistive and fluorinated acid resistive properties formed over said conductive member;
- a clad layer formed over the cobalt including layer for cladding said cobalt including layer; and
- a layer including oxygen formed over the clad layer.

2. (Previously Amended) The semiconductor device as cited in Claim 1, wherein said cobalt including layer is comprised of a cobalt tungsten phosphor layer.

3. (Previously Amended) The semiconductor device as cited in Claim 1, wherein said clad layer is comprised of a cobalt silicide layer.

4. (Previously Amended) The semiconductor device as cited in Claim 1, wherein said cobalt including layer is formed on a copper wiring.

5. (Previously Amended) A method for manufacturing a semiconductor device comprising the steps of:

- forming a cobalt including layer on a conductive member;
- forming a cobalt silicide layer on a surface of the cobalt including layer in a single processing step wherein said cobalt silicide layer is formed by exposing said cobalt including

layer in a silane system gas such that the source of the cobalt is the cobalt including layer and the source of the silicon is the silane gas.

6. (Original) The method of claim 5, further comprising forming a silicon oxide layer on the cobalt silicide by adding oxygen to the silane gas atmosphere.

7. (Original) The method as cited in claim 5, wherein said cobalt including layer is a cobalt tungsten phosphor layer.

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cont.

8. (Previously Amended) A semiconductor device comprising:

a conductive member;

a layer of CoWP formed over the conductive member;

a layer of cobalt silicide formed over the layer of CoWP; and

a silicon dioxide layer formed directly on the cobalt silicide.

9. (Previously Added) The semiconductor device of claim 8, wherein the conductive member is a copper wiring.

10. (Previously Canceled)

11. (Previously Added) The method of claim 5, wherein the conductor is a copper wiring.

12. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a cobalt including layer on a conductive member;

forming a cobalt silicide layer on a surface of the cobalt including layer by use of a silane gas atmosphere; and

forming a layer including oxygen directly on the cobalt silicide layer by adding oxygen to the silane gas atmosphere.

13. (Currently Amended) The semiconductor device of claim ~~1~~ 12, wherein the layer including oxygen is an oxide layer.
